

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Specification.

Please insert the following paragraph beginning on page 12, line 8.

a1 FIG. 4 is a cross-sectional view of a portion of a DRAM after various processing steps according to an embodiment.

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Please replace the paragraph beginning on page 2, line 15 with the following.

a2 A first interlayer insulating film 26 is formed on word line 22. A cell contact hole is formed between word lines 22 to expose the silicon substrate 12 through first interlayer insulating film 26. Cell contact hole is filled with an electrically conductive material  
10 such as DOPOS and tungsten (W) to form a cell contact plug 30.